

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Yukihito OOWAKI et al. )  
) Prior Application: Rule 53(b) Divisional of  
) Serial No.:09/340,149  
Serial No.: Not Yet Assigned ) filed June 28, 1999  
)  
Filed: June 13, 2001 ) Prior Group Art Unit: 2814  
)  
) Prior Examiner: NGO, N.  
)  
For: MIS TRANSISTOR AND METHOD) )  
FOR PRODUCING SAME )

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

**PRELIMINARY AMENDMENT**

Prior to the examination of the above application, please amend this application as follows:

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Page 12, second full paragraph, lines 13-20, replace with the following:

A<sup>2</sup>  
~Then, as shown in FIG. 3C, after a thin sacrificial oxide film 11 is laminated on the surfaces of the SiO<sub>2</sub> film 9 and the groove 4 of the silicon substrate, a polycrystalline silicon 10 is